

IN THE SPECIFICATION

Please amend the paragraph at page 3, line 11, as follows:

Due to the relative ease of growing planar Ga-face c-planes, virtually all GaN-based devices are grown parallel to the polar c-axis. Furthermore, strain at interfaces between adjacent dissimilar layers gives rise to piezoelectric polarization. The total polarization is a sum of the spontaneous and piezoelectric contributions, the net effect of which causes charge separation within quantum heterostructures. Charge separation within quantum wells decreases the electron-hole recombination efficiency and red-shifts the emission wavelength [see References 4-8], both of which are undesirable in the operation of the operation of light-emitting optoelectronic devices. It is believed that the efficiency of GaN light emitting devices would be enhanced were it possible to eliminate the polarization effects inherent to c-axis oriented devices.

Please add a new paragraph at page 13, line 10, as follows:

It should be noted that the substrate or template need not be uniformly planar for the practice of the invention. The substrate or template may be comprised of a patterned surface encouraging growth of the a-plane GaN film that occurs preferentially on selected areas or regions of the surface.

Please amend the paragraph at page 13, line 13, as follows:

The preferred embodiment describes an HVPE-based growth process utilizing a reaction between metallic gallium (Ga) and gaseous hydrogen chloride ([[GaCl]] HCl) as the Group III source. Alternative Group III sources, such as but not limited to, gallium trichloride (GaCl<sub>3</sub>), or alternative reactive gases, such as but not limited to, hydrogen bromide (HBr), may be used in the practice of this invention without fundamentally altering the method.